

SEMITOP® 3

IGBT Module

SK30GAD066T

Target Data

Features

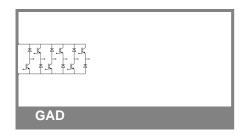
- · Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench silicon structure
- High short circuit capability
- Low tail current with low temperature dependence
- Integrated PTC temperature sensor

Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

Remarks

 PTC temp sensor test conditions: measuring current:1 mA max measuring current value: 3 mA



Absolute Maximum Ratings $T_s = 25 ^{\circ}\text{C}$, unless otherwise specifie					
Symbol	Conditions		Values	Units	
IGBT				•	
V_{CES}	T _j = 25 °C		600	V	
I _C	T _j = 175 °C	T _s = 25 °C	38	Α	
		$T_s = 70 ^{\circ}C$	31	Α	
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		60	Α	
V _{GES}			± 20	V	
t _{psc}	V_{CC} = 360 V; $V_{GE} \le 20$ V; $V_{CES} < 600$ V	T _j = 125 °C	6	μs	
Inverse [Diode			•	
I_{F}	T _j = 150 °C	$T_s = 25 ^{\circ}C$		Α	
		$T_s = 80 ^{\circ}C$		Α	
I _{FRM}	I _{FRM} = 2 x I _{Fnom}			Α	
Freewhe	eling Diode				
I_{F}	T _j = 175 °C	$T_{case} = 25 ^{\circ}C$	65	Α	
		T _{case} = 70 °C	51	Α	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$		200	Α	
Module					
I _{t(RMS)}				Α	
T_{vj}			-40 + 175	°C	
T _{stg}			-40 +125	°C	
V _{isol}	AC, 1 min.		2500	V	

Characteristics $T_s =$			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.43$ mA		5	5,8	6,5	V	
I _{CES}	$V_{GE} = 0 V, V_{CE} = V_{CES}$	T _j = 25 °C			0,08	mA	
		T _j = 125 °C				mA	
I _{GES}	V _{CE} = 0 V, V _{GE} = 30 V	T _j = 25 °C			300	nA	
		T _j = 125 °C				nA	
V _{CE0}		T _i = 25 °C		0,9	1	V	
		T _j = 150 °C		0,85	0,9	V	
r _{CE}	V _{GE} = 15 V	T _j = 25°C		18	28	mΩ	
		$T_{j} = 150^{\circ}C$		27	38	mΩ	
V _{CE(sat)}	I _{Cnom} = 30 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		1,45	1,85	V	
		$T_j = 150^{\circ}C_{chiplev.}$		1,65	2,05	V	
C _{ies}						nF	
C _{oes}	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz				nF	
C _{res}						nF	
$t_{d(on)}$						ns	
t _r	$R_{Gon} = 22 \Omega$	V _{CC} = 300V		4.04		ns	
E _{on}	D = 22.0	I _C = 30A		1,24		mJ	
$t_{d(off)} \ t_{f}$	$R_{Goff} = 22 \Omega$	T _j = 150 °C V _{GE} =±15V				ns ns	
E _{off}		GE ±10V		1,48		mJ	
R _{th(j-s)}	per IGBT	1		1,8		K/W	



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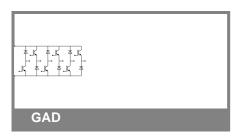
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Characteristics								
Symbol	Conditions		min.	typ.	max.	Units		
Freewheeling Diode								
$V_F = V_{EC}$	I_{Fnom} = 30 A; V_{GE} = 0 V			1,3	1,5	V		
		$T_j = 125 ^{\circ}C_{chiplev.}$		1,2	1,45	V		
V_{F0}		T _j = 125 °C		0,85	0,9	V		
r _F		T _j = 125 °C		9	16	mΩ		
I _{RRM}	I _F = 30 A	T _i = 125 °C		3		Α		
Q_{rr}	di/dt = -500 A/μs	,		3		μC		
E _{rr}	V _{CC} = 300V			0,44		mJ		
$R_{th(j-s)FD}$	per diode				1,2	K/W		
M_s	to heat sink M1		2,25		2,5	Nm		
w				30		g		
Temperature sensor								
R _{ts}	3%, T _r = 25 (100)°C			1000 (1670)		Ω		

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

